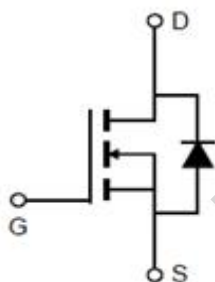
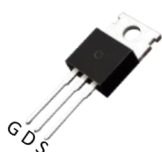


SGT N-channel Power MOSFET

MTR6R8N06CT
TO-220CB



V_{DS}	60	V
$R_{DS(on),TYP@ V_{GS}=10V}$	5.4	mΩ
I_D	72	A

Features

- 1、Low on – resistance
- 2、Package TO-220CB
- 3、SGT N-channel Power MOSFET

Applications

- 1、Load Switch for Portable Devices
- 2、DC/DC Converter

Maximum ratings, at $T_A = 25^\circ\text{C}$, unless otherwise specified

Symbol	Parameter		Rating	Unit
$V_{(BR)DSS}$	Drain-Source breakdown voltage		60	V
V_{GS}	Gate-Source voltage		± 20	V
I_D	Continuous drain current @ $V_{GS}=10V$	$T_C=25^\circ\text{C}$	72	A
		$T_C=100^\circ\text{C}$	56	A
I_{AS}	Avalanche Current		60	A
I_{DM}	Pulse drain current tested ①	$T_C=25^\circ\text{C}$	260	A
E_{AS}	Avalanche energy, single pulsed ②		180	mJ
P_D	Maximum power dissipation	$T_C=25^\circ\text{C}$	115	W
		$T_C=100^\circ\text{C}$	57.5	
T_{STG}, T_J	Storage and Junction Temperature Range		-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Typical	Unit
R _{θJC}	Thermal Resistance, Junction-to-Case	1.3	°C/W
R _{θJA}	Thermal Resistance, Junction-to-Ambient	60	°C/W

Electrical Characteristics

Symbol	Parameter	Condition	Min.	Typ.	Max.	Unit
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Static Electrical Characteristics @ T_j=25°C (unless otherwise stated)

V(BR)DSS	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	60	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =60V, V _{GS} =0V	--	--	1	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±20V, V _{DS} =0V	--	--	±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	2.5	3.0	3.5	V
R _{DS(on)}	Drain-Source On-State Resistance ④	V _{GS} =10V, I _D =20A	--	5.4	6.8	mΩ
g _{FS}	Forward Transconductance	V _{DS} =5V, I _D =20A	--	75	--	S
I _S	Maximum Body-Diode Continuous Current		--	--	72	A

Dynamic Electrical Characteristics @ T_j = 25°C (unless otherwise stated)

C _{iss}	Input Capacitance	V _{DS} =30V, V _{GS} =0V, f=1MHz	--	4050	--	pF
C _{oss}	Output Capacitance		--	345	--	pF
C _{rss}	Reverse Transfer Capacitance		--	16.8	--	pF
R _g	Gate Resistance	V _{GS} =0V, f=1MHz, V _{DS} =0V	0.3	0.65	1.0	Ω
Q _g (10V)	Total Gate Charge	V _{DS} =30V, I _D =20A, V _{GS} =10V	--	53	75	nC
Q _{gs}	Gate-Source Charge		--	17	--	nC
Q _{gd}	Gate-Drain Charge		--	5	--	nC

Switching Characteristics

Td(on)	Turn-on Delay Time	V _{DS} =30V, V _{GS} =10V, R _L =1.5Ω, R _{GEN} =3Ω	--	18	--	ns
Tr	Turn-on Rise Time		--	20	--	ns
Td(off)	Turn-Off Delay Time		--	33	--	ns
Tf	Turn-Off Fall Time		--	4	--	ns

Source- Drain Diode Characteristics@ T_j = 25°C (unless otherwise stated)

VSD	Forward on voltage	I _{SD} =1A, V _{GS} =0V	--	0.7	1	V
Trr	Reverse Recovery Time	I _F =20A, di/dt=500A/μs	--	26	--	ns
Qrr	Reverse Recovery Charge	I _F =20A, di/dt=500A/μs	--	125	--	nC

NOTE: ① Repetitive rating; pulse width limited by max junction temperature.

② Limited by T_{Jmax}, starting T_J = 25°C, L = 0.1mH. Part not recommended for use above this value

③ The power dissipation P_{DSM} is based on R_{θJA} and the maximum allowed junction temperature of 150°C.

④ Pulse width ≤ 380μs; duty cycle ≤ 2%.

Typical Characteristics

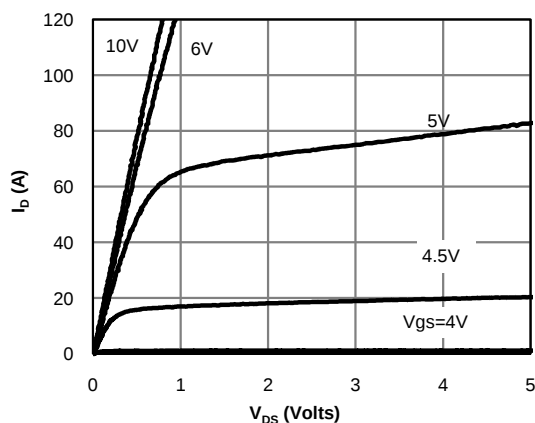


Fig 1: On-Region Characteristics

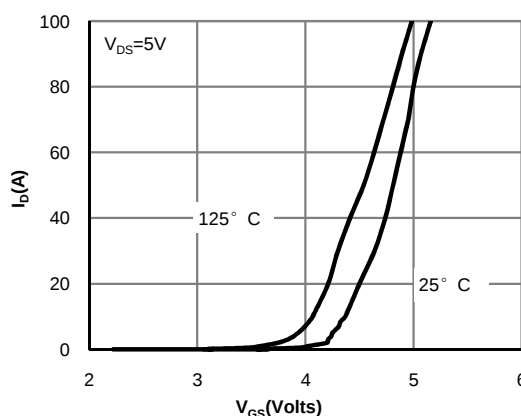


Figure 2: Transfer Characteristics

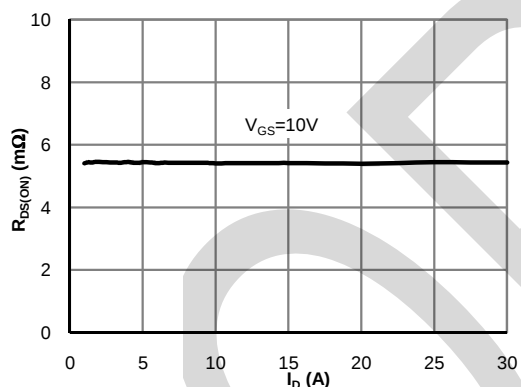


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

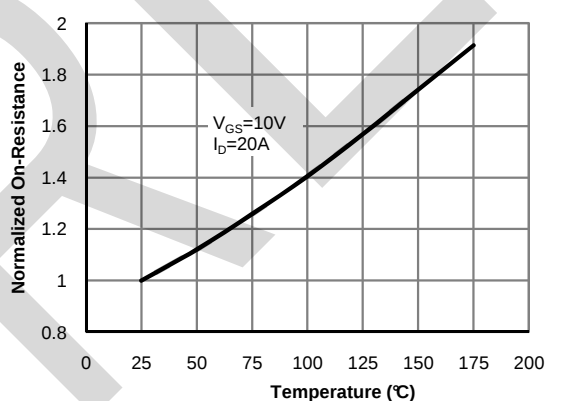


Figure 4: On-Resistance vs. Junction Temperature

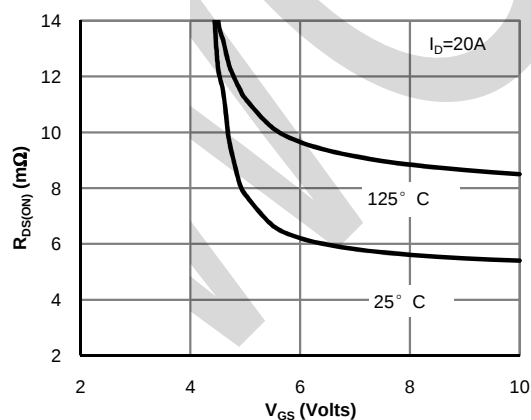


Figure 5: On-Resistance vs. Gate-Source Voltage

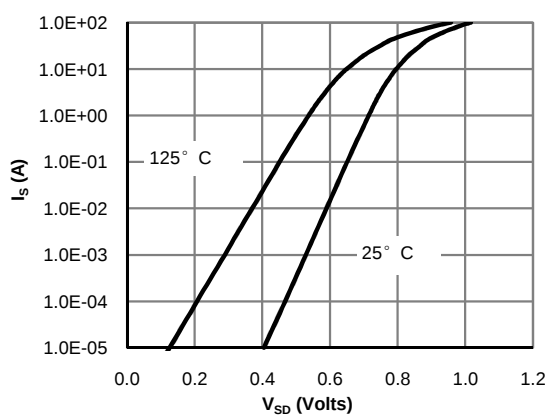


Figure 6: Body-Diode Characteristics

Typical Characteristics

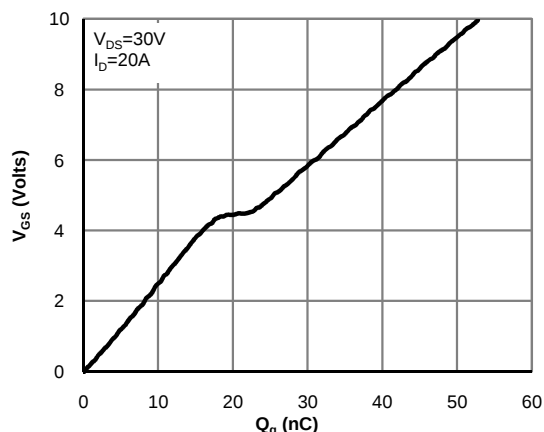


Figure 7: Gate-Charge Characteristics

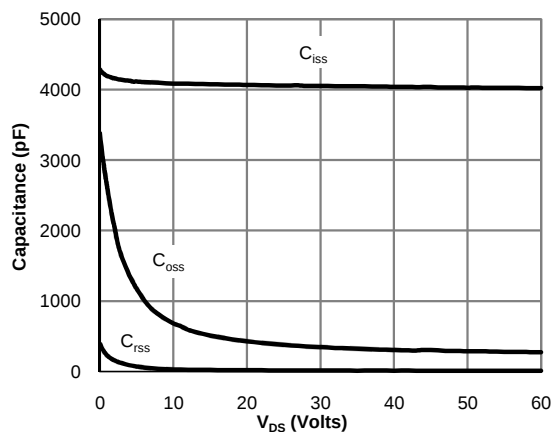


Figure 8: Capacitance Characteristics

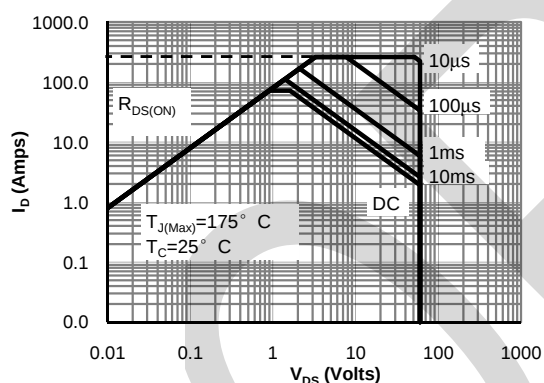


Figure 9: Maximum Forward Biased Safe Operating Area

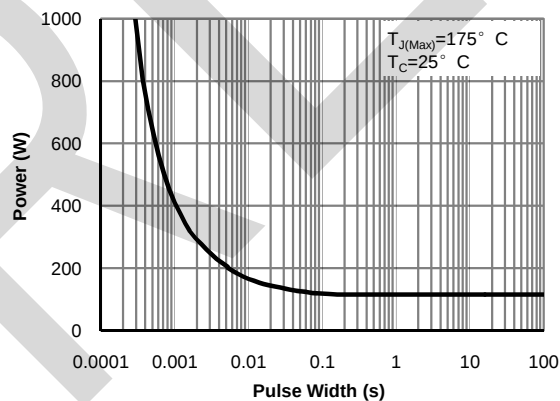


Figure 10: Single Pulse Power Rating Junction-to-Case

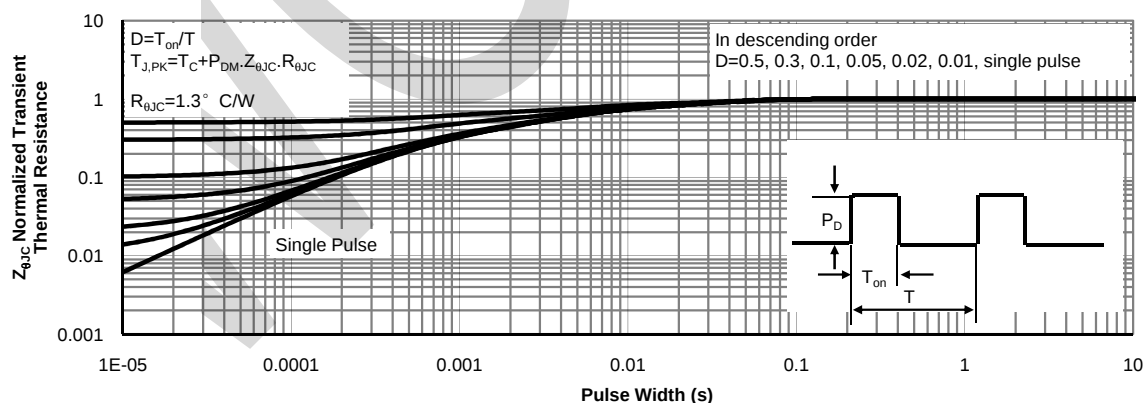
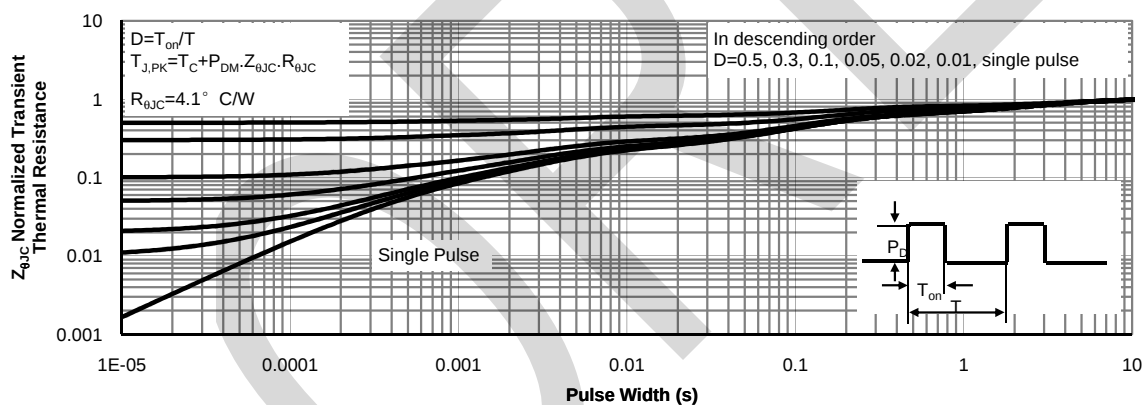
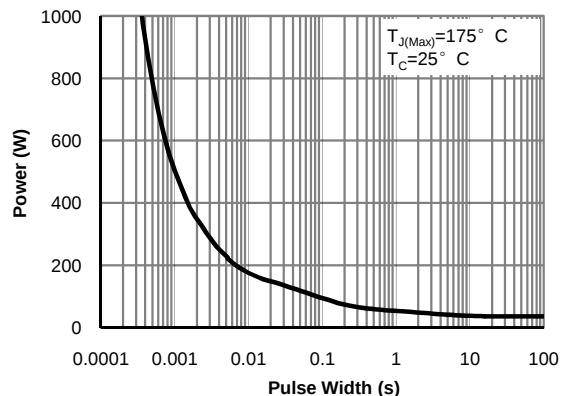
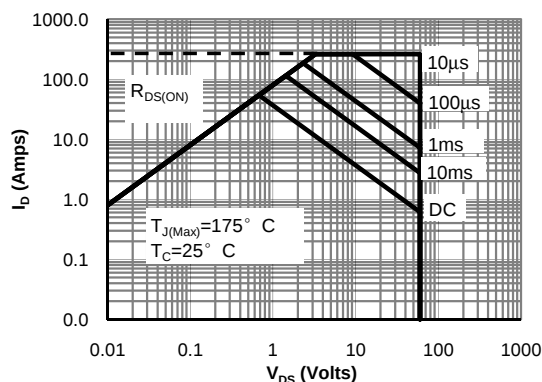


Figure 11: Normalized Maximum Transient Thermal Impedance

Typical Characteristics



Typical Characteristics

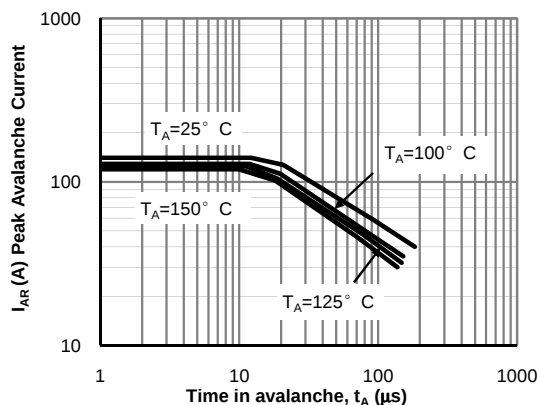


Figure 12: Single Pulse Avalanche capability

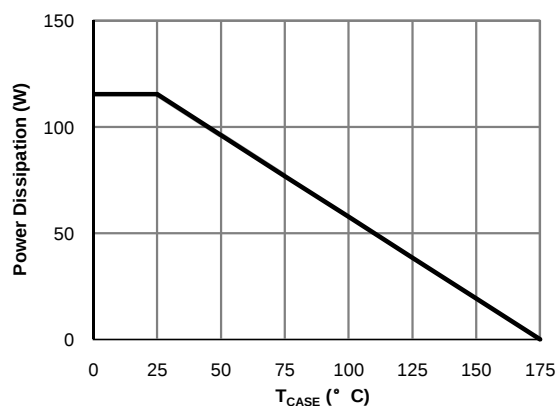


Figure 13: Power De-rating

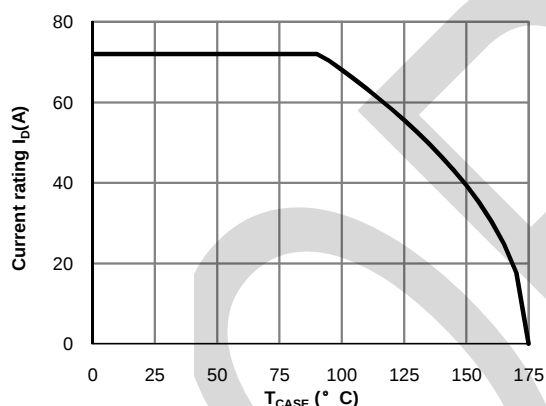


Figure 14: Current De-rating

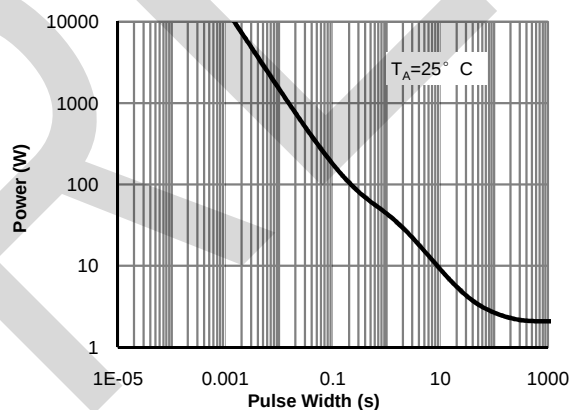


Figure 15: Single Pulse Power Rating Junction-to-Ambient

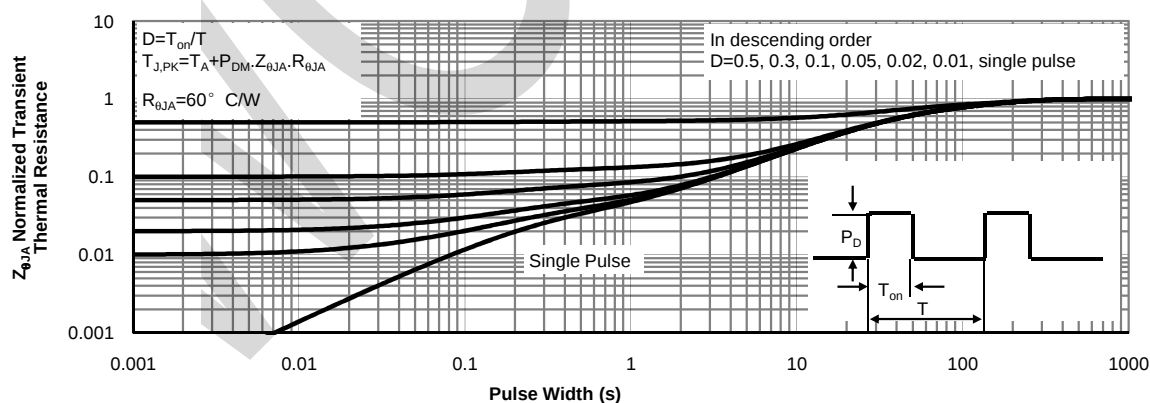
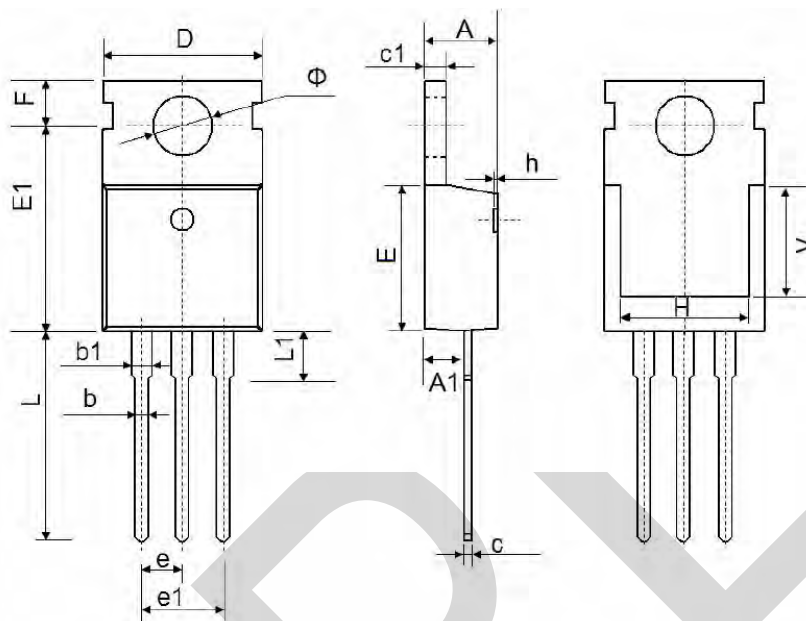


Figure 16: Normalized Maximum Transient Thermal Impedance

PACKAGE OUTLINE DIMENSIONS

TO-220CB



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.400	4.600	0.173	0.181
A1	2.250	2.550	0.089	0.100
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.330	0.650	0.013	0.026
c1	1.200	1.400	0.047	0.055
D	9.910	10.250	0.390	0.404
E	8.9500	9.750	0.352	0.384
E1	12.650	12.950	0.498	0.510
e	2.540 Typ.		0.100 Typ.	
e1	4.980	5.180	0.196	0.204
F	2.650	2.950	0.104	0.116
H	7.900	8.100	0.311	0.319
h	0.000	0.300	0.000	0.012
L	12.900	13.400	0.508	0.528
L1	2.850	3.250	0.112	0.128
V	7.500 Ref.		0.295 Ref.	
Φ	3.400	3.800	0.134	0.150